

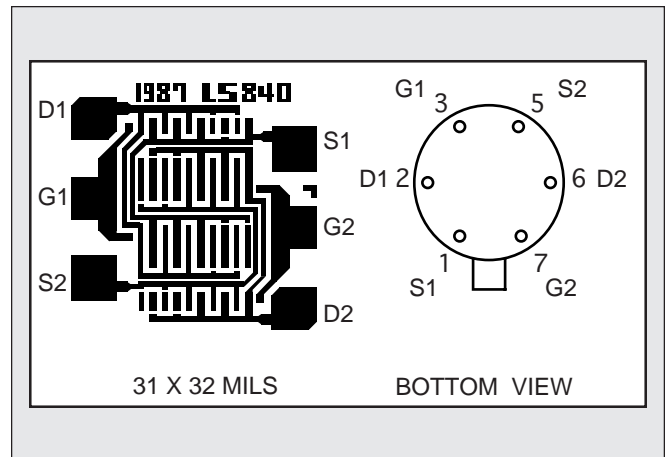
LINEAR SYSTEMS

Linear Integrated Systems

LS840 LS841 LS842

LOW NOISE LOW DRIFT
LOW CAPACITANCE
MONOLITHIC DUAL N-CANNEL JFET

FEATURES		
LOW NOISE	$e_n = 8nV/\sqrt{Hz}$ TYP.	
LOW LEAKAGE	$I_G = 10pA$ TYP.	
LOW DRIFT	$ \Delta V_{GS1-2}/\Delta T = 5\mu V/^\circ C$ max.	
LOW OFFSET VOLTAGE	$ V_{GS1-2} = 2mV$ TYP.	
ABSOLUTE MAXIMUM RATINGS NOTE 1		
@ 25°C (unless otherwise noted)		
Maximum Temperatures		
Storage Temperature	-65° to +150°C	
Operating Junction Temperature	+150°C	
Maximum Voltage and Current for Each Transistor NOTE 1		
$-V_{GSS}$	Gate Voltage to Drain or Source	60V
$-V_{DSO}$	Drain to Source Voltage	60V
$-I_{G(f)}$	Gate Forward Current	50mA
Maximum Power Dissipation		
Device Dissipation @ Free Air - Total	400mW @ +125°C	

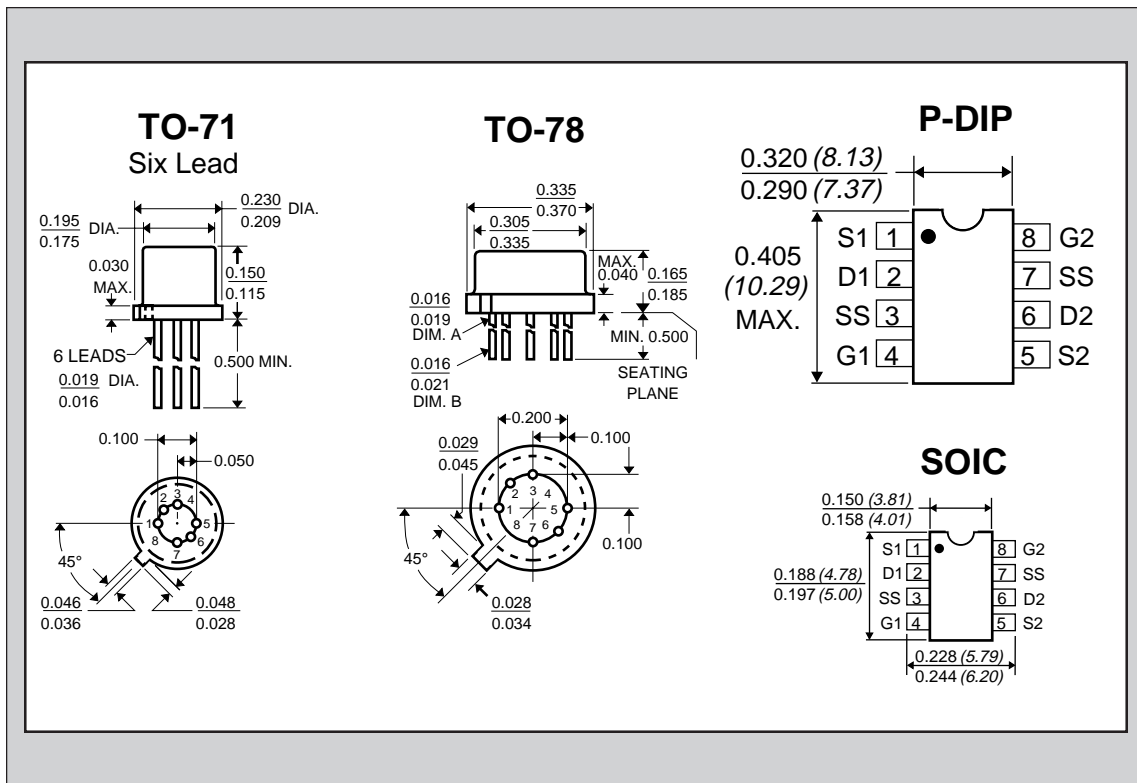


ELECTRICAL CHARACTERISTICS @ 25°C (unless otherwise noted)

SYMBOL	CHARACTERISTICS	LS840	LS841	LS842	UNITS	CONDITIONS
$ \Delta V_{GS1-2}/\Delta T $ max.	Drift vs. Temperature	5	10	40	$\mu V/^\circ C$	$V_{DG} = 20V$ $T_A = -55^\circ C$ to $+125^\circ C$ $I_D = 200\mu A$
$ V_{GS1-2} $ max.	Offset Voltage	5	10	25	mV	$V_{DG} = 20V$ $I_D = 200\mu A$

SYMBOL	CHARACTERISTICS	MIN.	TYP.	MAX.	UNITS	CONDITIONS
BV_{GSS}	Breakdown Voltage	60	--	--	V	$V_{DS} = 0$ $I_D = 1nA$
BV_{GGO}	Gate-to-Gate Breakdown	60	--	--	V	$I_G = 1nA$ $I_D = 0$ $I_S = 0$
TRANSCONDUCTANCE						
Y_{fss}	Full Conduction	1000	--	4000	μmho	$V_{DG} = 20V$ $V_{GS} = 0$ $f = 1kHz$
Y_{fs}	Typical Conduction	500	--	1000	μmho	$V_{DG} = 20V$ $I_D = 200\mu A$
$ Y_{fs1-2}/Y_{fs} $	Mismatch	--	0.6	3	%	
DRAIN CURRENT						
I_{DSS}	Full Conduction	0.5	2	5	mA	$V_{DG} = 20V$ $V_{GS} = 0$
$ I_{DSS1-2}/I_{DSS} $	Mismatch at Full Conduction	--	1	5	%	
GATE VOLTAGE						
$V_{GS(off)}$ or V_P	Pinchoff Voltage	1	2	4.5	V	$V_{DS} = 20V$ $I_D = 1nA$
V_{GS}	Operating Range	0.5	--	4	V	$V_{DS} = 20V$ $I_D = 200\mu A$
GATE CURRENT						
$-I_G$	Operating	--	10	50	pA	$V_{DG} = 20V$ $I_D = 200\mu A$
$-I_G$	High Temperature	--	--	50	nA	$V_{DG} = 20V$ $I_D = 200\mu A$ $T_A = +125^\circ C$
$-I_G$	Reduced VDG	--	5	--	pA	$V_{DG} = 10V$ $I_D = 200\mu A$
$-I_{GSS}$	At Full Conduction	--	--	100	pA	$V_{DG} = 20V$ $V_{DS} = 0$

SYMBOL	CHARACTERISTICS	MIN.	TYP.	MAX.	UNITS	CONDITIONS
OUTPUT CONDUCTANCE						
Y_{OSS}	Full Conduction	--	--	10	μmho	$V_{DG} = 20V$ $V_{GS} = 0$
Y_{OS}	Operating	--	0.1	1	μmho	$V_{DG} = 20V$ $I_D = 200\mu A$
$ Y_{OS1-2} $	Differential	--	0.01	0.1	μmho	
COMMON MODE REJECTION						
CMR	$-20 \log \Delta V_{GS1-2} / \Delta V_{DS} $	--	100	--	dB	$\Delta V_{DS} = 10 \text{ to } 20V$ $I_D = 200\mu A$
CMR		--	75	--	dB	$\Delta V_{DS} = 5 \text{ to } 10V$ $I_D = 200\mu A$
NOISE						
NF	Figure	--	--	0.5	dB	$V_{DS} = 20V$ $V_{GS} = 0$ $R_G = 10M\Omega$ $f = 100\text{Hz}$ $NBW = 6\text{Hz}$
e_n	Voltage	--	--	10	$\text{nV}/\sqrt{\text{Hz}}$	$V_{DS} = 20V$ $I_D = 200\mu A$ $f = 1\text{KHz}$ $NBW = 1\text{Hz}$
e_n	Voltage	--	--	15	$\text{nV}/\sqrt{\text{Hz}}$	$V_{DS} = 20V$ $I_D = 200\mu A$ $f = 10\text{Hz}$ $NBW = 1\text{Hz}$
CAPACITANCE						
C_{ISS}	Input	--	4	10	pF	$V_{DS} = 20V$ $I_D = 200\mu A$
C_{RSS}	Reverse Transfer	--	1.2	5	pF	
C_{DD}	Drain-to-Drain	--	0.1	--	pF	$V_{DG} = 20V$ $I_D = 200\mu A$



NOTES:

1. These ratings are limiting values above which the serviceability of any semiconductor may be impaired.